P-Channel 100-V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ.)
- 100	0.200 at V_{GS} = - 10 V	- 3.0	13.2 nC
	0.230 at V_{GS} = - 6 V	- 2.4	

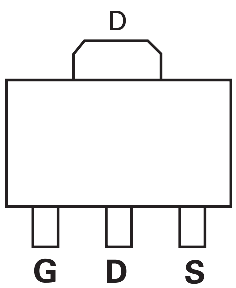
FEATURES

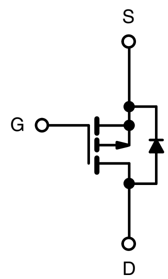
- Trench Power MOSFET
- 100% R_g and UIS Tested

RoHS COMPLIANT
HALOGEN FREE Available

APPLICATIONS

- Active Clamp in Intermediate DC/ DC Power Supplies
- H-Bridge High Side Switch for Lighting Application





P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	- 100	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	- 3.0	A
	T_C = 70 °C		-2.1	
	T_A = 25 °C		- 2[a, b]	
	T_A = 70 °C		- 1.6[a, b]	
Pulsed Drain Current		I_{DM}	- 12	
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	- 4.9	
	T_A = 25 °C		- 2.5[a, b]	
Avalanche Current	L = 0.1 mH	I_{AS}	- 15	
Single-Pulse Avalanche Energy		E_{AS}	11.25	mJ
Maximum Power Dissipation	T_C = 25 °C	P_D	6.5	W
	T_C = 70 °C		4.8	
	T_A = 25 °C		3.1[a, b]	
	T_A = 70 °C		2[a, b]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

Notes:
a. Surface mounted on 1" x 1" FR4 board.
b. t = 10 s.

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[a, b]	t ≤ 10 s	R_{thJA}	33	40	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	17	21	

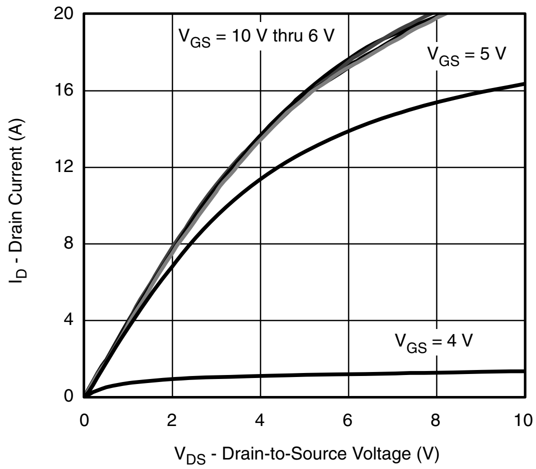
Notes:
a. Surface mounted on 1" x 1" FR4 board.
b. Maximum under steady state conditions is 80 °C/W.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = - 250 µA	- 100			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = - 250 µA		- 165		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 6.6		
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA	- 2		- 4	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 100 V, V_{GS} = 0 V			- 1	µA
		V_{DS} = - 100 V, V_{GS} = 0 V, T_J = 55 °C			- 10	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \geq$ - 5 V, V_{GS} = - 10 V	- 8			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = - 10 V, I_D = - 3 A		0.200		Ω
		V_{GS} = - 6 V, I_D = - 2 A		0.230		
Forward Transconductance[a]	g_{fs}	V_{DS} = - 15 V, I_D = 3 A		12		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = - 35 V, V_{GS} = 0 V, f = 1 MHz		819		pF
Output Capacitance	C_{oss}			51		
Reverse Transfer Capacitance	C_{rss}			32		
Total Gate Charge	Q_g	V_{DS} = - 50 V, V_{GS} = - 10 V, I_D = - 3 A		17.5	32	nC
		V_{DS} = - 50 V, V_{GS} = - 6 V, I_D = - 3 A		13.2	25	
Gate-Source Charge	Q_{gs}			3.4		
Gate-Drain Charge	Q_{gd}			6.4		
Gate Resistance	R_g	f = 1 MHz		6.1	9.2	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 50 V, R_L = 25 Ω $I_D \cong$ - 3 A, V_{GEN} = - 6 V, R_g = 1 Ω		10	20	ns
Rise Time	t_r			55	95	
Turn-Off DelayTime	$t_{d(off)}$			20	40	
Fall Time	t_f			15	30	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 50 V, R_L = 25 Ω $I_D \cong$ - 3 A, V_{GEN} = - 10 V, R_g = 1 Ω		11	18	
Rise Time	t_r			18	32	
Turn-Off DelayTime	$t_{d(off)}$			32	58	
Fall Time	t_f			20	35	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C			- 13	A
Pulse Diode Forward Current[a]	I_{SM}				- 15	
Body Diode Voltage	V_{SD}	I_S = - 3 A		- 0.8	- 1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = - 3 A, dI/dt = 100 A/µs, T_J = 25 °C		65	90	ns
Body Diode Reverse Recovery Charge	Q_{rr}			180	270	nC
Reverse Recovery Fall Time	t_a			45		ns
Reverse Recovery Rise Time	t_b			20		

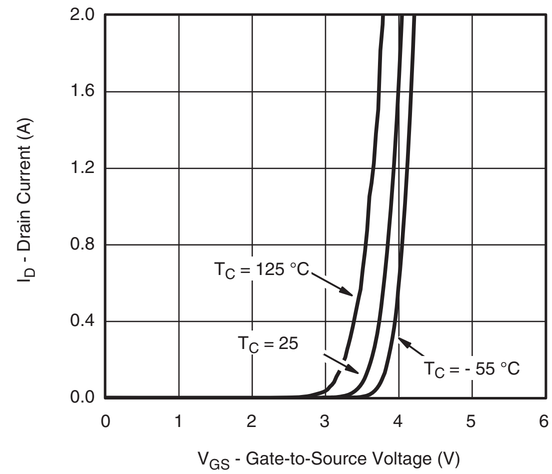
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

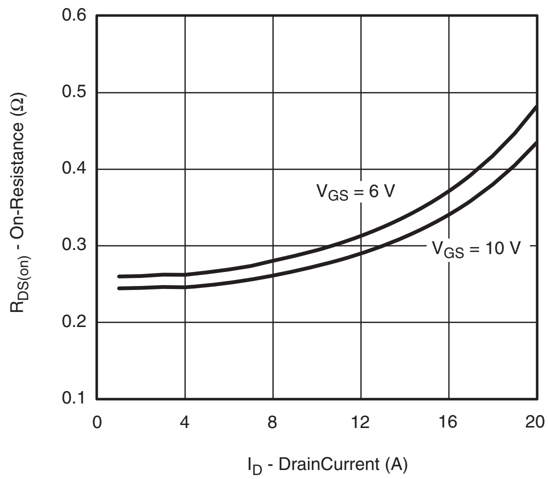
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



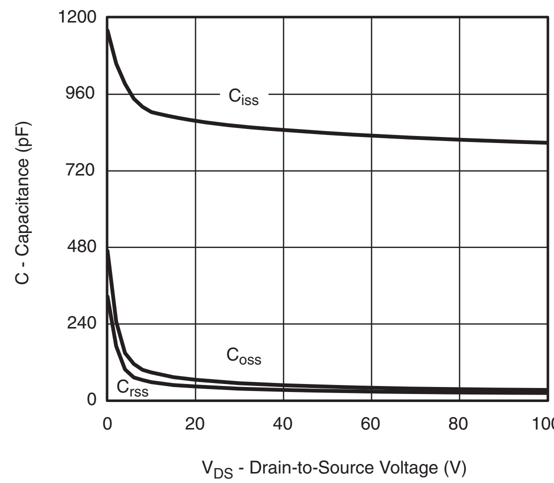
Output Characteristics



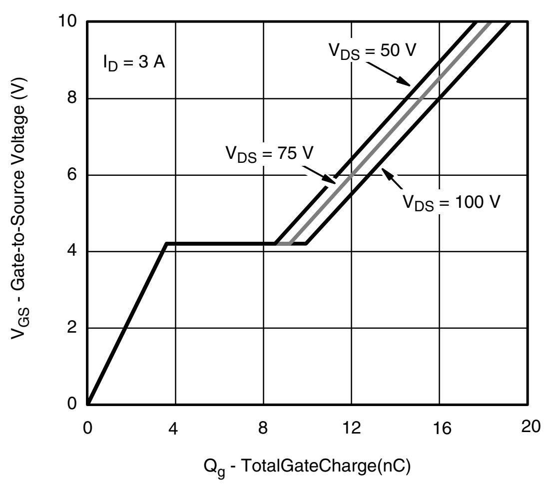
Transfer Characteristics



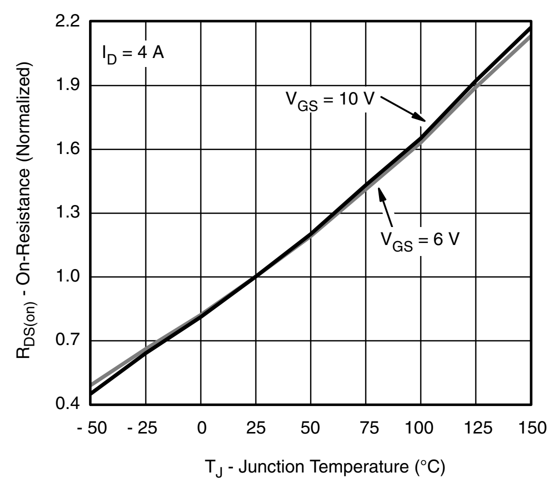
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

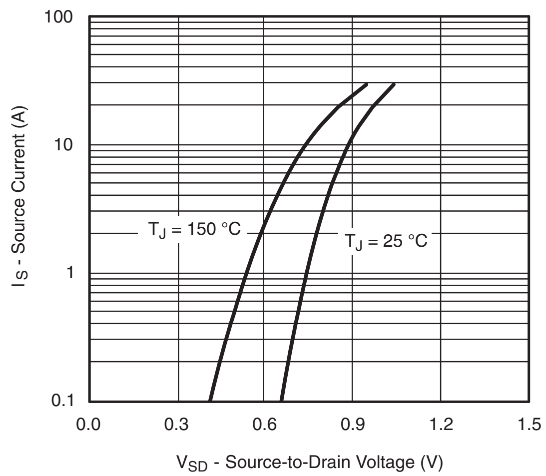


Gate Charge

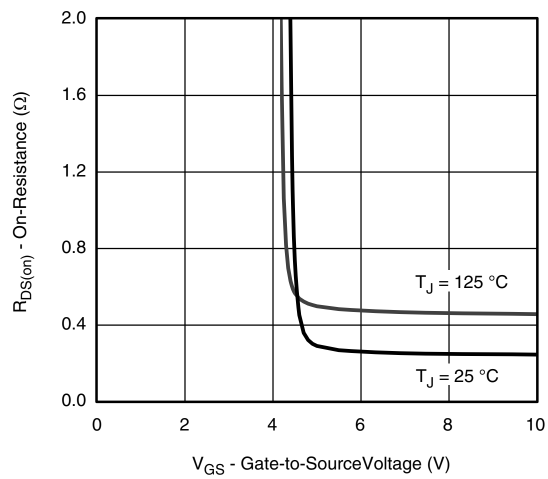


On-Resistance vs. Junction Temperature

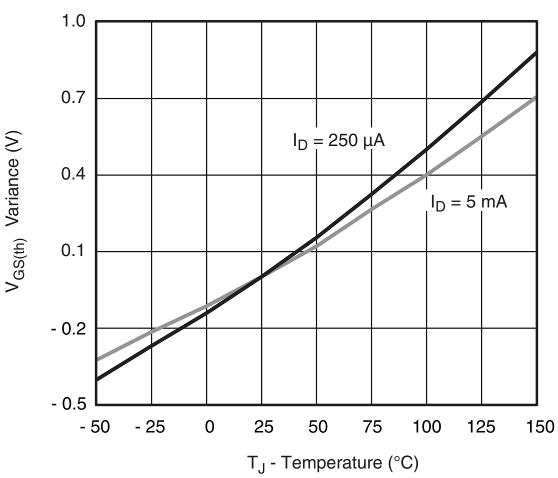
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



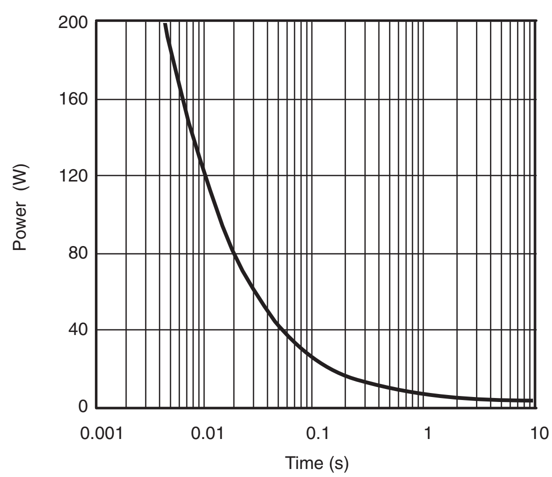
Source-Drain Diode Forward Voltage



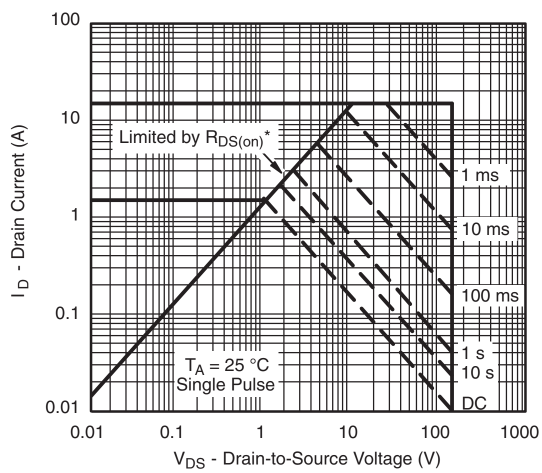
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

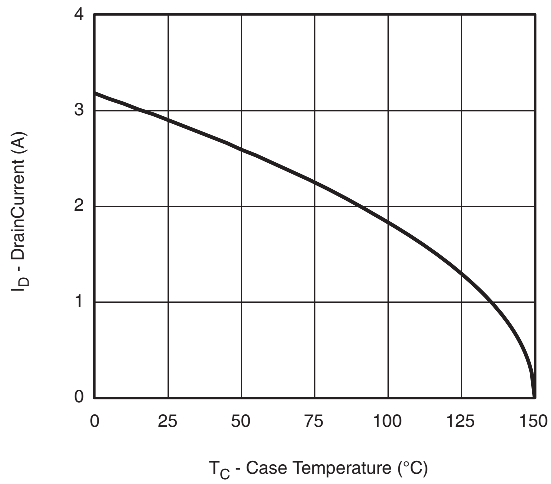


Single Pulse Power, Junction-to-Ambient

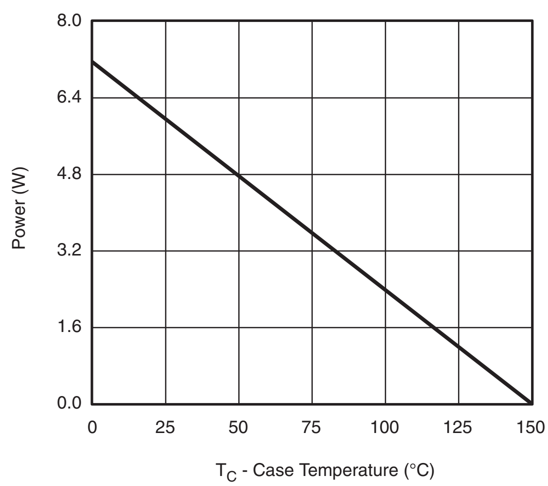


Safe Operating Area, Junction-to-Ambient

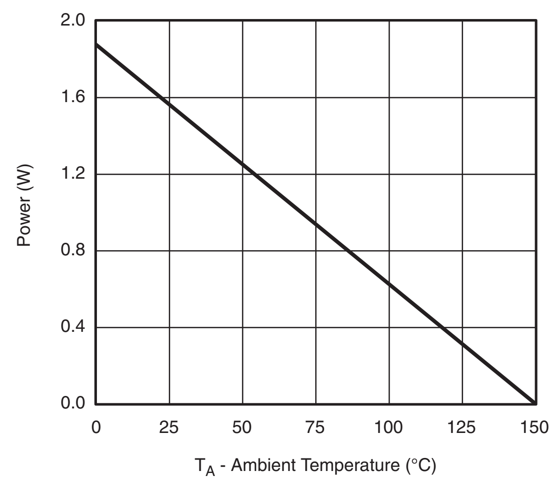
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



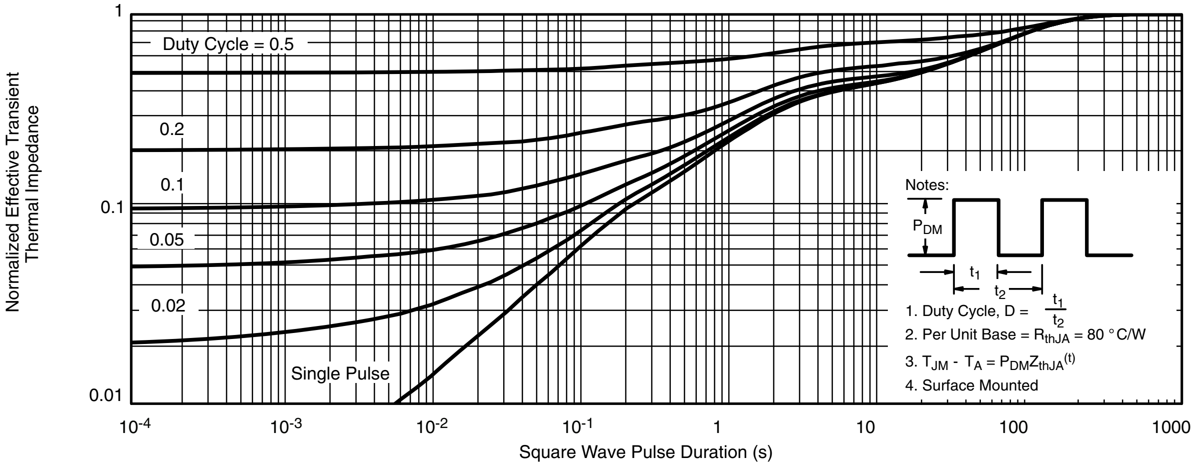
Power, Junction-to-Foot



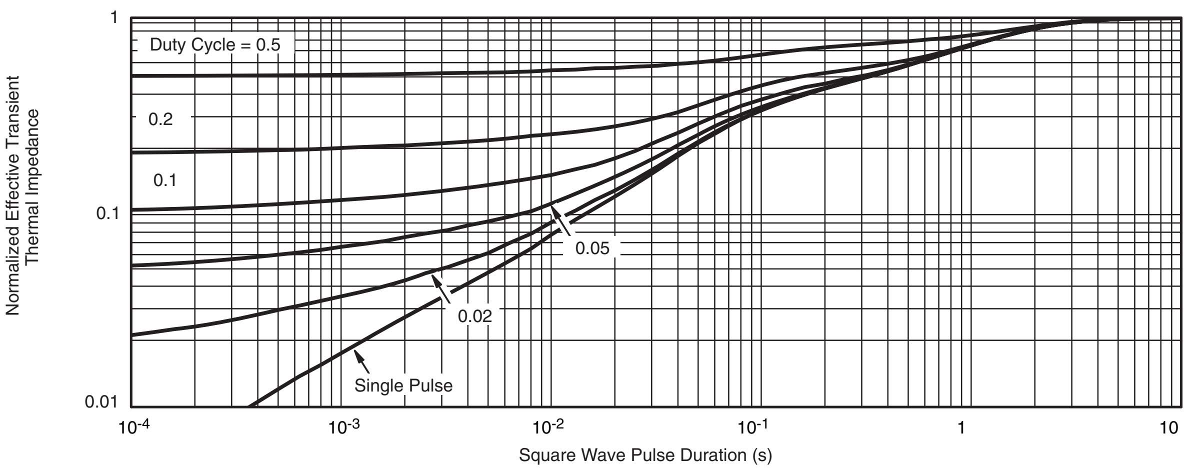
Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max.)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

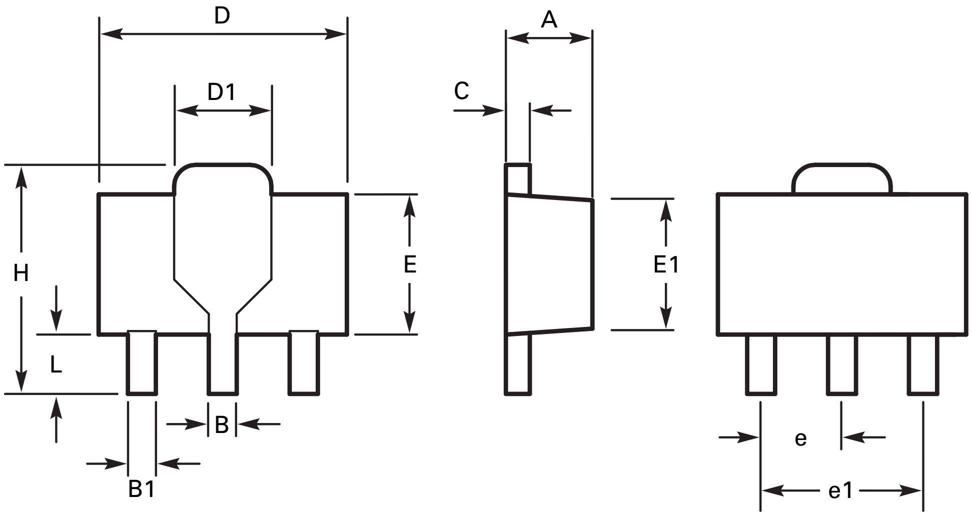


Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Package outline - SOT89



DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	1.40	1.60	0.550	0.630	E	2.29	2.60	0.090	0.102
B	0.44	0.56	0.017	0.022	E1	2.13	2.29	0.084	0.090
B1	0.36	0.48	0.014	0.019	e	1.50 BSC		0.059 BSC	
C	0.35	0.44	0.014	0.017	e1	3.00 BSC		0.118 BSC	
D	4.40	4.60	0.173	0.181	H	3.94	4.25	0.155	0.167
D1	1.62	1.83	0.064	0.072	L	0.89	1.20	0.035	0.047

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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